

forming a first conductive layer of a material which is substantially unetchable by chemical dry-etching;

forming a second conductive layer on the first conductive layer from a material which is etchable by chemical dry-etching;

structuring the second conductive layer to form a structured second layer; and

dry etching the first conductive layer while using the second structured layer as a mask.

Claim 8 (amended). The method according to claim 1, further comprising:

applying at least one insulation layer on the electrode configuration, and structuring the insulation layer to form at least one contact hole to the electrode configuration; and

depositing a conductive layer and filling in the contact hole.

Claim 14 (amended). The method according to claim 1, further comprising chemical dry etching the second conductive layer while using the first structured layer as a barrier for the chemical dry-etching.

Enter The Following New Claims:

-- 21. The method according to claim 1, wherein the material for forming the first conductive layer is selected from the group consisting of a 4d transition metal, a 5d transition metal, a conductive nitride thereof, and a conductive oxide thereof.

22. The method according to claim 1, wherein the material for forming the first conductive layer is selected from the group of platinum metals. --